

COMPOUND FIELD EFFECT POWER TRANSISTOR

μ PA1604

MONOLITHIC POWER MOS FET ARRAY

DESCRIPTION

The μ PA1604 is Monolithic N-channel Power MOS FET Array that built in 4 circuits, Clump Diode and resistances designed for LED, Relay, Thermal Head, and so on.

FEATURES

- Direct driving is possible by standard Logic IC or Microcomputer.
(4 V driving is possible)
- Output Voltage: $V_{O(\text{peak})} = 50 \text{ V MAX}$.
Output Current: $I_{O(\text{peak})} = 1.5 \text{ A MAX}$.
- $R_{on} = 1 \Omega \text{ TYP. at: } I_o = 600 \text{ mA, } V_i = 4.5 \text{ V}$
- Wide Operation Temperature: $-40 \text{ to } +85^\circ\text{C}$
- Output Voltage Clump Diode built in.
- Low Input Active

ORDERING INFORMATION

| Part Number | Package | Quality Grade |
|----------------|------------|---------------|
| μ PA1604CX | 16-Pin DIP | Standard |

Please refer to "Quality grade on NEC Semiconductor Devices" (Document number IEI-1209) published by NEC Corporation to know the specification of quality grade on the devices and its recommended applications.

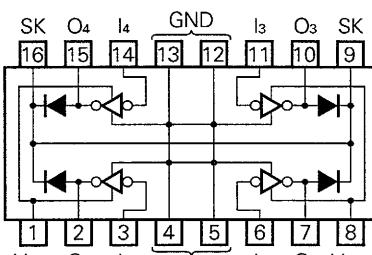
ABSOLUTE MAXIMUM RATINGS ($T_a = 25^\circ\text{C}$)

| | | | |
|--------------------------|-----------------------|------------------------|------------------|
| Supply Voltage | V_{DD} | -0.5 to +7.0 | V |
| Output Voltage | $V_{O(\text{DC})}$ | 30 | V |
| Output Peak Voltage* | $V_{O(\text{peak})}$ | 50 | V |
| Input Voltage | V_i | -0.5 to $V_{DD} + 0.5$ | V |
| Output Current (DC) | $I_{O(\text{DC})}$ | 870 | mA/unit |
| Output Current (pulse)** | $I_{O(\text{pulse})}$ | 1500 | mA/unit |
| Input Current | I_i | ± 10 | mA/unit |
| Diode Reverse Voltage | V_R | 50 | V |
| Diode Forward Current | I_F | 1500 | mA/unit |
| Total Power Dissipation | P_D | 1.0 | W/PKG |
| Operating Temperature | T_{opt} | -40 to +85 | $^\circ\text{C}$ |
| Storage Temperature | T_{stg} | -55 to +150 | $^\circ\text{C}$ |

* PW $\leq 10 \text{ ms}$, Duty Cycle $\leq 50 \%$

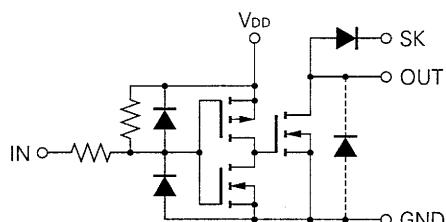
** PW $\leq 10 \text{ ms}$, Duty Cycle $\leq 30 \%$

CONNECTION DIAGRAM



I : Input
O : Output
 V_{DD} : Supply Voltage

Equivalent Circuits (1/8 Circuit)



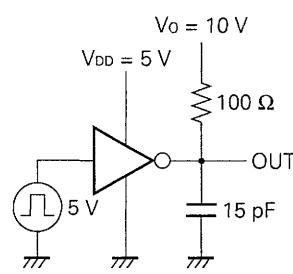
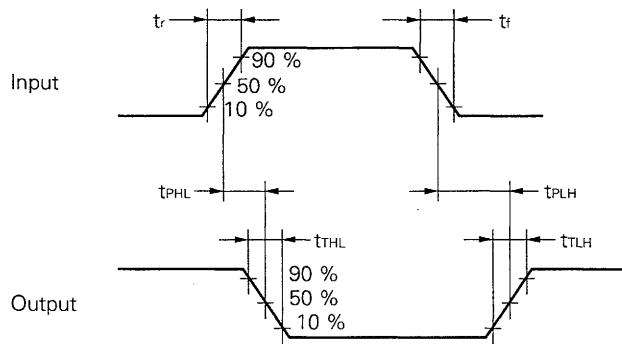
RECOMMENDED OPERATING CONDITIONS ($T_a = -40$ to $+85$ °C)

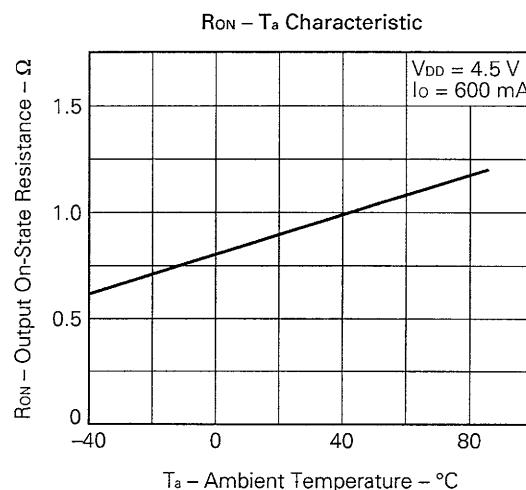
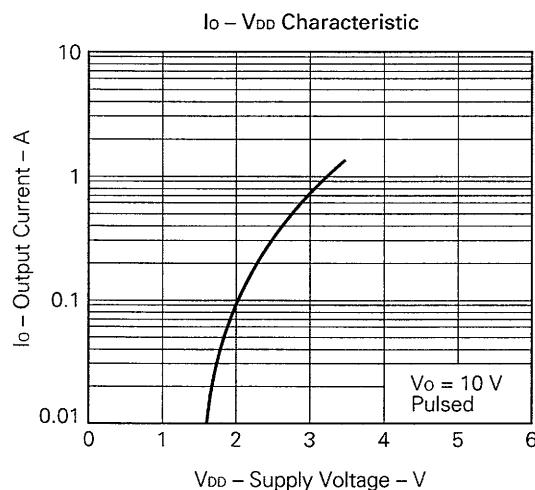
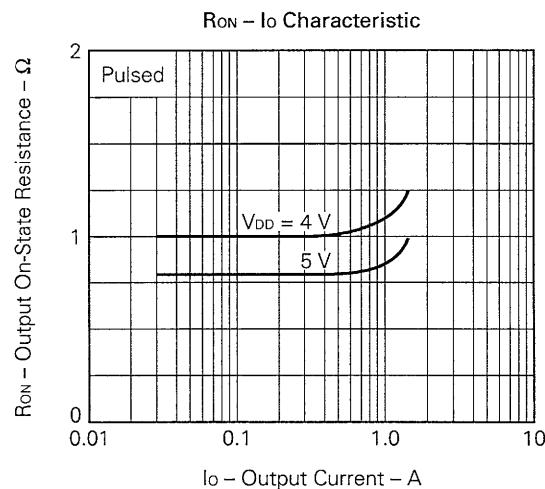
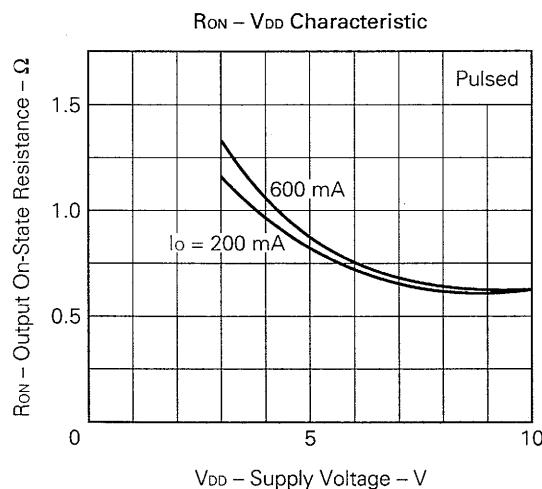
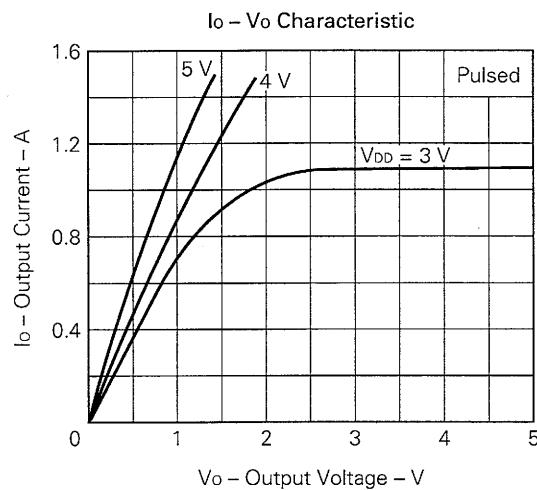
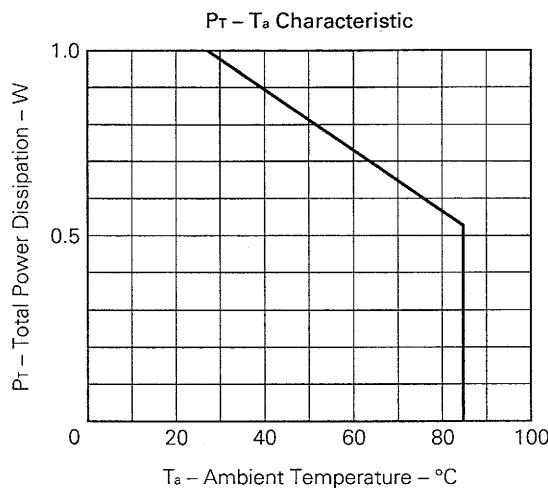
| CHARACTERISTIC | SYMBOL | MIN. | TYP. | MAX. | UNIT | TEST CONDITIONS |
|--------------------------|--------------|------|------|------|---------|---|
| Supply Voltage | V_{DD} | 4.5 | 5.0 | 5.5 | V | |
| Output Voltage | $V_{O(DC)}$ | | | 28 | V | |
| Output Current | $I_{O(DC)}$ | | | 540 | mA/unit | DC, 1 circuit |
| | $I_O(pulse)$ | | | 600 | mA/unit | $PW \leq 10$ ms, Duty Cycle $\leq 20\%$, 4 circuits |
| Input Voltage | V_I | 0 | | 5 | V | |
| High-Level Input Voltage | V_{IH} | 2 | | | V | |
| Low-Level Input Voltage | V_{IL} | | | 0.8 | V | |
| Diode Reverse Voltage | V_R | | | 40 | V | |
| Diode Forward Current | I_F | | | 600 | mA | |

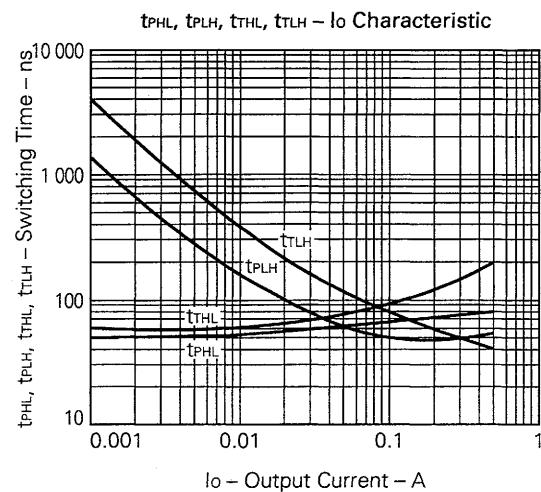
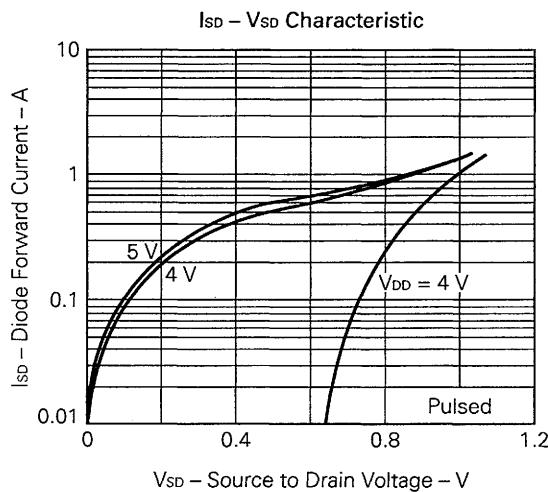
ELECTRICAL CHARACTERISTICS ($T_a = 25$ °C)

| CHARACTERISTIC | SYMBOL | MIN. | TYP. | MAX. | UNIT | TEST CONDITIONS |
|----------------------------|---------------|------|------|------|----------|---|
| Supply Voltage | $I_{DD(ON)}$ | | | 1 | mA | $V_{DD} = 5.5$ V, $V_I = 0$ |
| | $I_{DD(OFF)}$ | | | 10 | μ A | $V_{DD} = 5.5$ V, $V_I = 5.5$ V |
| Output Leakage Current | $I_O(OFF)$ | | | 10 | μ A | $V_{DD} = 5.5$ V, $V_I = 5.5$ V, $V_O = 50$ V |
| Output On-state Resistance | R_{on} | | 1 | 1.3 | Ω | $V_{DD} = 4.5$ V, $V_I = 0$, $I_O = 600$ mA |
| Output On-state Voltage | $V_{O(ON)1}$ | | | 0.1 | V | $V_{DD} = 4.5$ V, $V_I = 0$, $I_O = 10$ mA |
| | $V_{O(ON)2}$ | | | 1.0 | V | $V_{DD} = 4.5$ V, $V_I = 0$, $I_O = 600$ mA |
| Input Voltage | $V_{I(OFF)}$ | 2 | | | V | $V_{DD} = 5$ V, $V_O = 50$ V, $I_O = 100$ μ A |
| | $V_{I(ON)1}$ | | | 0.8 | V | $V_{DD} = 5$ V, $V_O = 0.8$ V, $I_O = 1$ mA |
| Input Current | I_{IH} | | | 10 | μ A | $V_{DD} = 5.5$ V, $V_I = 5.5$ V, $V_O = 0$ V |
| | I_{IL} | | | -1 | mA | $V_{DD} = 5.5$ V, $V_I = 0$ V, $V_O = 50$ V |
| Input Capacitance | C_{in} | | 10 | | pF | $f = 1$ MHz |
| Delay Time | t_{PHL} | | 70 | | ns | $V_{DD} = 5$ V, $R_L = 100$ Ω $V_O = 10$ V, $C_L = 15$ pF $t_r, t_f \leq 5$ ns See Fig. 1 |
| | t_{PLH} | | 50 | | ns | |
| Rise Time | t_{TLH} | | 40 | | ns | |
| Fall Time | t_{TLL} | | 110 | | ns | |
| Diode Leakage Current | I_R | | | 50 | μ A | $V_R = 50$ V, $T_a = 25$ °C |
| | | | | 100 | μ A | $V_R = 50$ V, $T_a = 85$ °C |
| Diode Forward Voltage | V_F | | | 2 | V | $I_F = 1.25$ A |

Fig. 1 Switching Wave Forms and Test Circuits



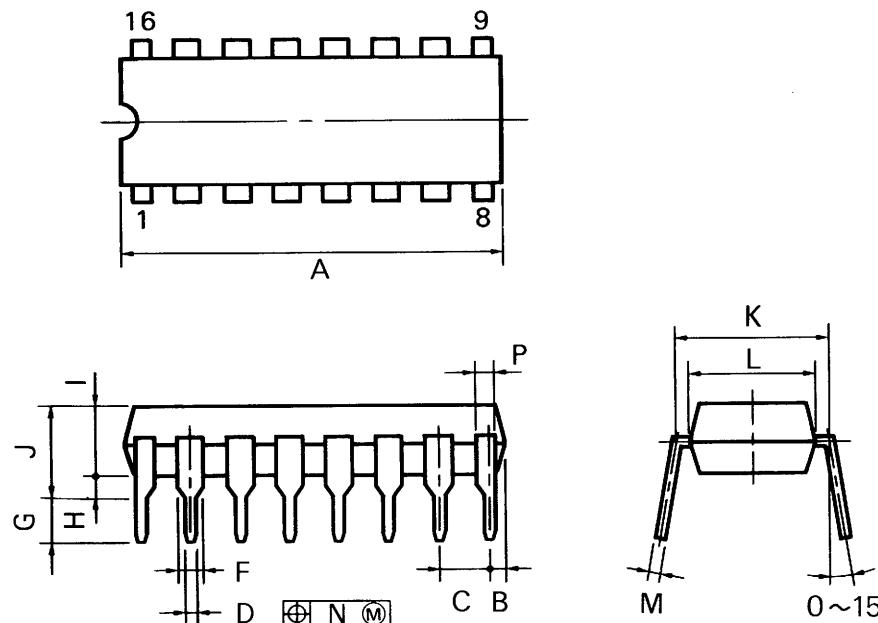
TYPICAL CHARACTERISTICS ($T_a = 25^\circ\text{C}$)



PACKAGE DIMENSIONS

- μ PA1604CX

16PIN PLASTIC DIP (300 mil)



NOTES

- 1) Each lead centerline is located within 0.25 mm (0.01 inch) of its true position (T.P.) at maximum material condition.
- 2) Item "K" to center of leads when formed parallel.

| ITEM | MILLIMETERS | INCHES |
|------|------------------------|---------------------------|
| A | 20.32 MAX. | 0.800 MAX. |
| B | 1.27 MAX. | 0.050 MAX. |
| C | 2.54 (T.P.) | 0.100 (T.P.) |
| D | $0.50^{+0.10}$ | $0.020^{+0.004}_{-0.005}$ |
| F | 1.2 MIN. | 0.047 MIN. |
| G | $3.5^{+0.3}$ | $0.138^{+0.012}$ |
| H | 0.51 MIN. | 0.020 MIN. |
| I | 4.31 MAX. | 0.170 MAX. |
| J | 5.08 MAX. | 0.200 MAX. |
| K | 7.62 (T.P.) | 0.300 (T.P.) |
| L | 6.4 | 0.252 |
| M | $0.25^{+0.10}_{-0.05}$ | $0.010^{+0.004}_{-0.003}$ |
| N | 0.25 | 0.01 |
| P | 1.0 MIN. | 0.039 MIN. |

RECOMMENDED SOLDERING CONDITIONS

The following conditions (see table below) must be met when soldering this product.

Please consult with our sales offices in case other soldering process is used, or in case soldering is done under different conditions.

TYPES OF THROUGH HOLE MOUNT DEVICE

μ PA1604CX

| Soldering process | Soldering conditions | Symbol |
|-------------------|--|--------|
| Wave soldering | Solder temperature: 260 °C or below, Flow time: 10 seconds or below | |

Reference

| Document name | Document No. |
|--|--------------|
| Quality control of NEC semiconductors devices. | TEI-1202 |
| Quality control guide of semiconductors devices. | MEI-1202 |
| Assembly manual of semiconductors devices. | IEI-1207 |
| Semiconductor device package manual | IEI-1213 |
| SMD surface mount technology manual | IEI-1207 |

[MEMO]

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Application examples recommended by NEC Corporation.

Standard: Computer, Office equipment, Communication equipment, Test and Measurement equipment, Machine tools, Industrial robots, Audio and Visual equipment, Other consumer products, etc.

Special: Automotive and Transportation equipment, Traffic control systems, Antidisaster systems, Anticrime systems, etc.